

Device Type	V _{RRM} (1)	V _{RSM} (1)
ZK720-10	1000	1100
ZK720-12	1200	1300
ZK720-14	1400	1500
ZK720-16	1600	1700
ZK720-18	1800	1900

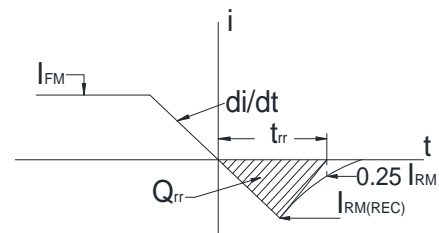
V_{RRM} = Repetitive peak reverse voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage current	I _{RRM}	15 mA 35 mA (3)
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Notes:

All ratings are specified for T_j=25 °C, unless otherwise stated

- (1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range -40°C to +125 °C.
- (2) 10 msec. max. pulse width
- (3) Maximum value for T_j = 125 °C.
- (4) See parameter definition below :



reverse recovery characteristic

Average forward current	I _{F(AV)}	720	A	Sinewave 180°, T _c =70	
RMS forward current	I _{FRMS}	1109	A		
Peak one cycle surge (non repetitive) current	I _{FSM}	8640	A	10 msec (50Hz), sinusoidal wave-shape, 180° conduction, T _j =125	
I square t	I ² t	37.3 10 ⁴	A ² s	8.3 msec and 10.0 msec	
Peak forward voltage	V _{FM}	2.40	V	I _{FM} = 2400A; Duty cycle 0.01%	
Threshold voltage	V _{FO}	1.30	V	T _j =125°C, I=0.5 I _{F(AV)} to 1.5 I _{F(AV)}	
Slope resistance	r _F	0.37	m	T _j =125°C, I=0.5 I _{F(AV)} to 1.5 I _{F(AV)}	
Reverse Recovery Current (4)	I _{RM(REC)}	*	A	I _{FM} = 1000 A; dI _F /dt = 10 A/ s; T _j max	
Reverse Recovery Charge (4)	Q _{rr}	*	μC	I _{FM} = 1000 A; dI _F /dt = 10 A/ s; T _j max	
Reverse Recovery Time (4)	t _{rr}	5	μs	I _{FM} = 1000 A; dI _F /dt = 10 A/ s; T _j max	

